## 計算科学とナノサイエンス

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計算科学研究センター・シンポジウム 平成16年6月11日

## なぜ大規模計算が必要?

## \*ナノ構造系の計算では必然的に大規模

特徴的なサイズ、外部系との相互作用実験のみでは攻め難い

\*原子や電子の過程と、応用したい性質現象機能が直に関連

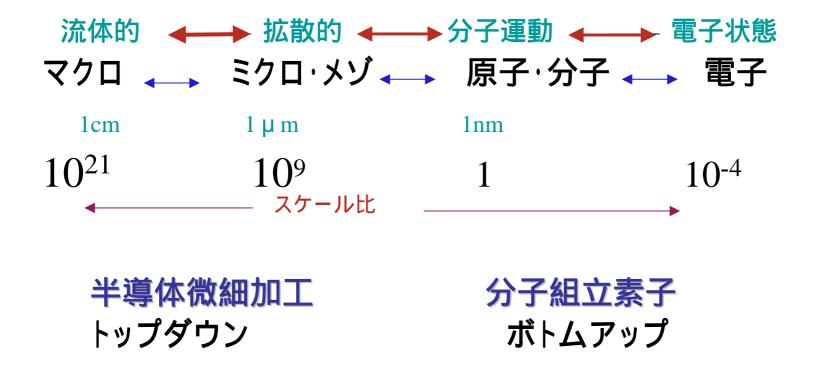
階層横断的なマルチフィジックス現象

実験研究と相補的役割 産業応用でも極めて重要

#### 例:

光合成系・太陽電池の 理論設計 電界放射、界面反応設計 光電気化学系、触媒設計 分子エレクトロニクスチ ナノバイオ系 量子メリカス系 ナノ材料機能開発 ナノ計測・制御

### 物質・材料設計における階層構造



## ナノ構造設計

分子量子デバイス / 分子発光・分子磁石 / N E M S / 分子機械 / 量子コンピュータ / ナノ構造デバイス設計 / ドラッグデリバリ系 / クラスター・CNT・フラーレン関連物質材料 / ナノ医療技術・材料 /

→→ 諸現象、生成法、物性、機能予測、 非平衡開放系、強相関現象、非線形現象、 分子+固体、無機+有機、

原子スケール ―― メゾ・マクロ

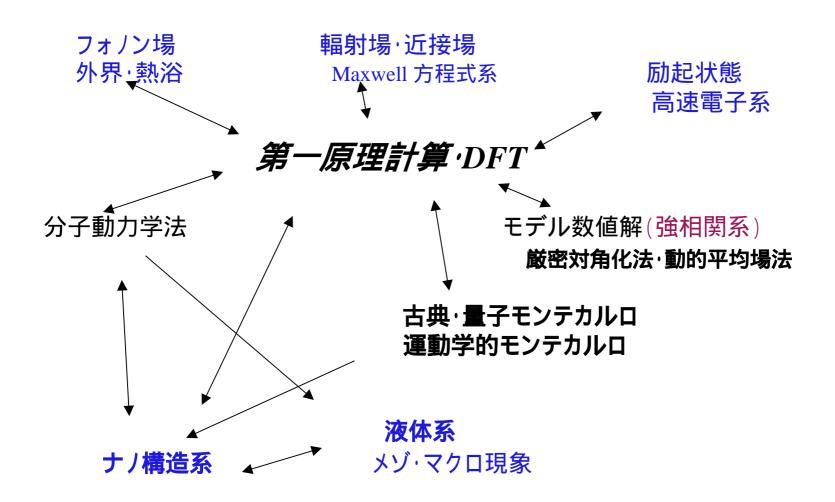
## 計算理論・計算技術の新展開

1)大規模計算へ向けての新しい手法

有限要素法、ハイブリッド法、 時間発展法、オーダN法、その他

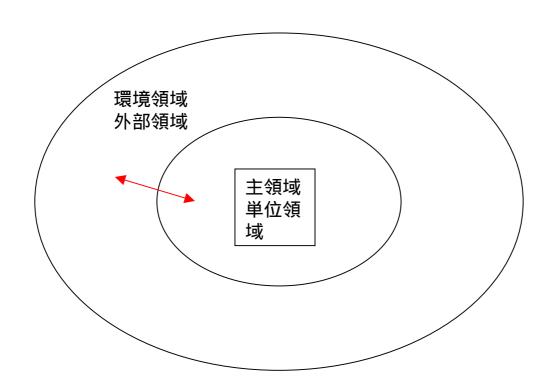
- 2)系の階層性をどう処理するか 階層連結のアルゴリズム?
- 3)第一原理法(密度汎関数法)の新しい展開 強相関をどう扱う? 原子振動と強く結合した系 非平衡系の散逸 外場(輻射場、局所磁場)との連成系をどう解くか?

## 計算手法における階層構造



# 時空の階層性、複雑さ・厳密さの階層性

遠方の扱い、熱浴・粒子浴、他自由度の扱い、繰り込み 励起系の扱い、水分子(生体系)



## 実空間有限要素法

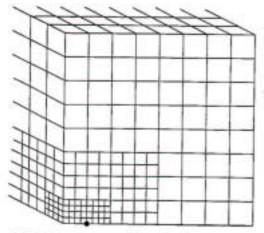


FIG. 4. In practice, we used the mesh twice as dense as this figure. The mesh is taken approximately logarithmic.

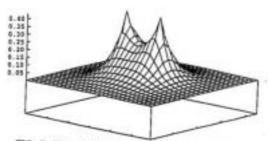


FIG. 5. The calculated electron density for the hydrogen molecule at the equilibrium bond length (in units eXbohr<sup>-1</sup>). The two peaks indicate the position of the nuclei. The singularity at the nucleus is well reproduced.

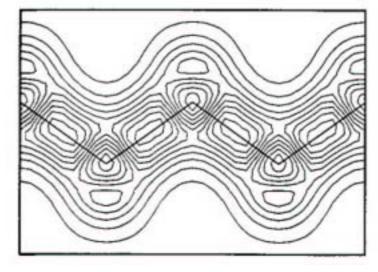


TABLE I. Properties of the hydrogen molecule. The other theory is from Ref. 20, in which LDA calculations are performed with Gaussian orbitals. The experimental data are from Ref. 21.

	Bond	length	(a.u.)	Vibrational	frequency	(cm <sup>-1</sup> )
This work		1.46	Trat-	11 1-24	4424	
Other theory		1.45 4277				
Experiment		1.40 4400				

TABLE II. Properties of Si in the diamond structure. The experimental data are from Refs. 31, 32, and 33 of Ref. 14.

	Lattice constant (a.u.)	Cohesive energy (eV/atom)	Bulk modulus (Mbar)
This work	10.43	4.76	0.94
Other theory	10.45	4.70	0.97
Experiment	10.26	4.63	0.99

E.Tsuchida and M.Tsukada Phys.Rev.B52(1995)5573-5578 Phys.Rev.B54(1996)7602-7605 J.Phys.Soc.Jpn.67(1998)3844-3858 Chem.Phys.Lett.311(1999)236-240

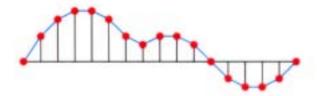
## 時間発展密度汎関数法

N.Watanabe and M.Tsukada PRE 62(2000)2914

Based on an Iterative method.

$$|\psi(t + \Delta t)\rangle = \exp\left[-i\frac{\Delta t}{\hbar}\mathcal{H}\right]|\psi(t)\rangle$$

Based on a Real space method.



Based on exponential product technique.

$$|\psi(t + \Delta t)\rangle = \left[\prod_{n} \exp\left[-i\Delta t \mathcal{H}_{n}\right]\right] |\psi(t)\rangle$$

Based on the Cayley method.

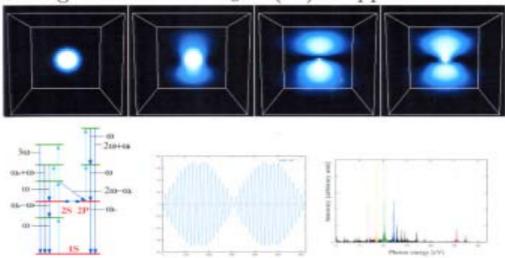
$$|\psi(t + \Delta t)\rangle = \frac{1 - i\Delta t \mathcal{H}/2}{1 + i\Delta t \mathcal{H}/2} |\psi(t)\rangle$$

Now we show our method in detail.

## 時間発展密度汎関数法の応用例

Excitation of Hydrogen atom:

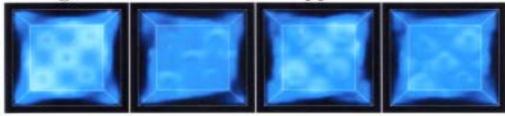
Strong electron field  $E_o \sin(\omega t)$  is applied

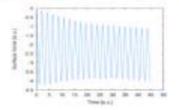


many optical processes cause non-linear scattering.

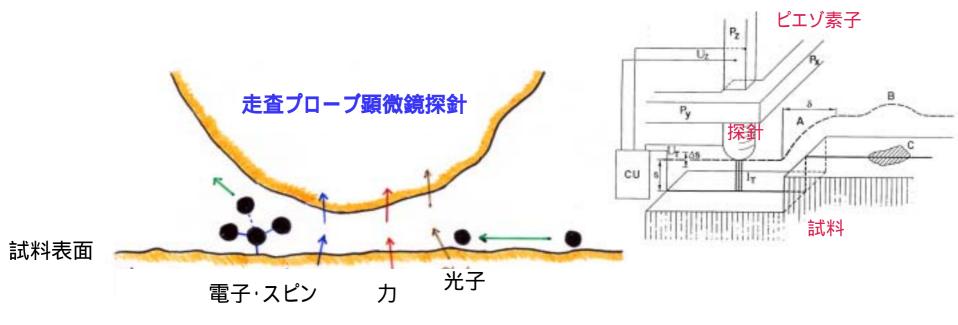
#### Solid plasma in diamond crystal:

Strong static electric field is applied





By taking account of the surface charge, the solid plasma occurs in the crystal.



走査プローブ顕微鏡(SPM) - STM, AFM, SNOM etc - は、対象物の何をどのように観るのか?

情報伝達機構、探針の原子構造・原子種の効果、定量解析法

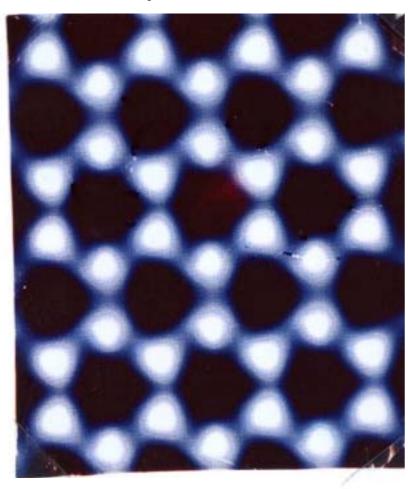
電子分光、 カスペクトル、 原子マニピュレーション

ナノ構造制御・機能開発

量子力学的第一原理計算(DFTなど)による理論シミュレーション

### Si(111) 3× 3-Ag 表面のSTM像 実験と理論

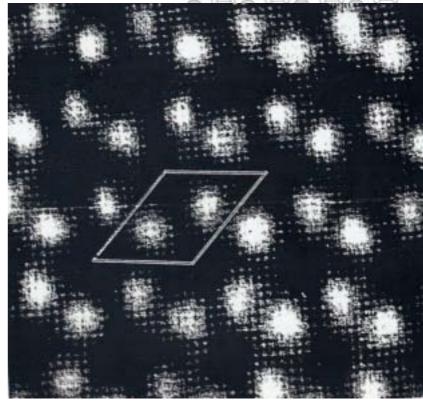
Theory HCT model



 $V_s=1V$ 

Unoccupied

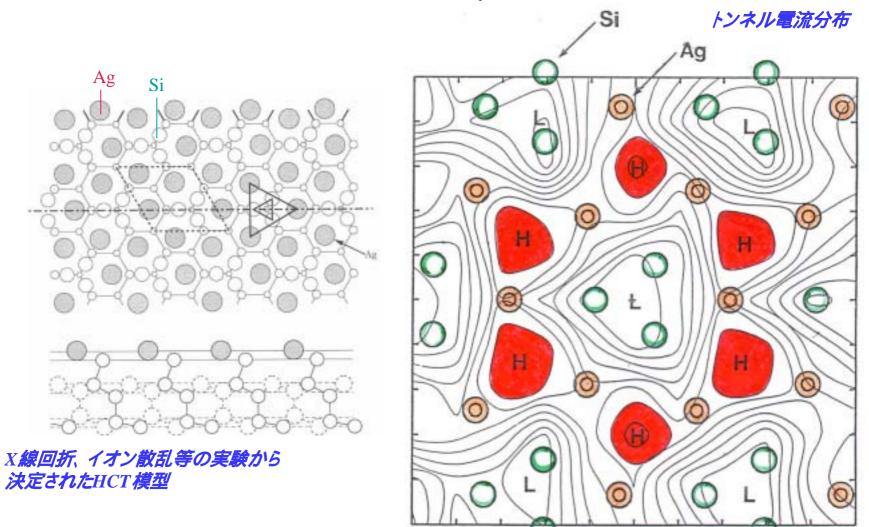
states



W<sub>10</sub>[111]**探針模型** Watanabe, Aono, Tsukada(1991) Phys.Rev.B44 (1991)8330

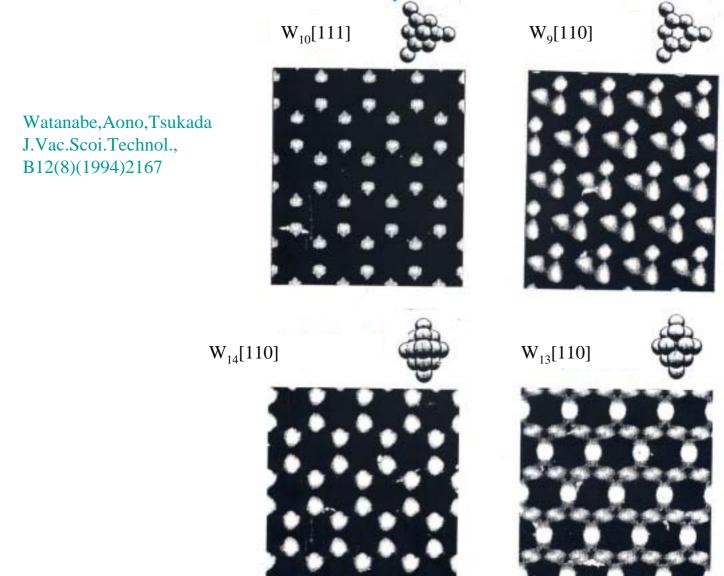
## Si(111) 3X 3-Ag 表面(HCT 模型)

Wartanabe, Aono, Tsukada(1991) Phys.Rev.B44 (1991)8330



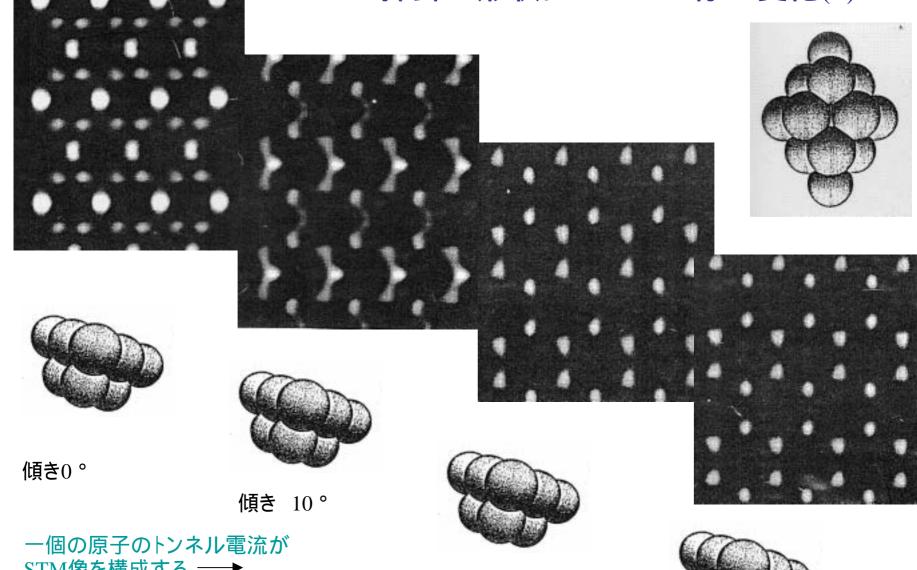
#### 探針の形状によるSTM像の変化(1)

(計算結果、V<sub>x=-1.0</sub>V)



探針先端の頂点原 子を除去すると STM像が大き(変 化する

## 探針の形状によるSTM像の変化(2)



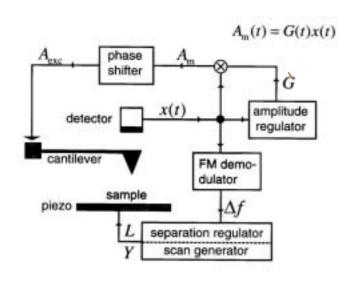
STM像を構成する → トライン 原子尺度分解能の機構

傾き20°

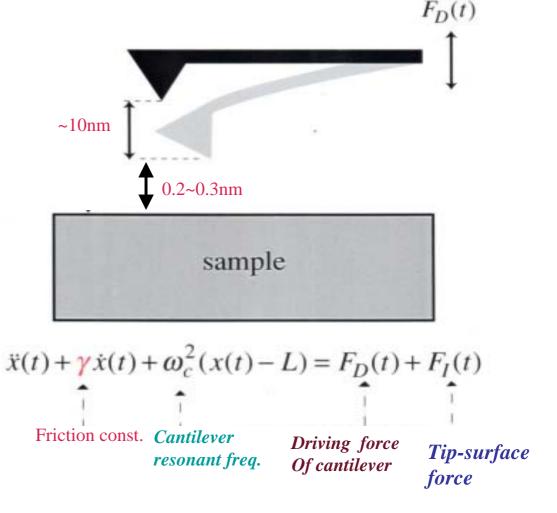
傾き30°

#### How the force by the individual atom can be observed?

Theory of non contact Atomic Force Microscopy (ncAFM)

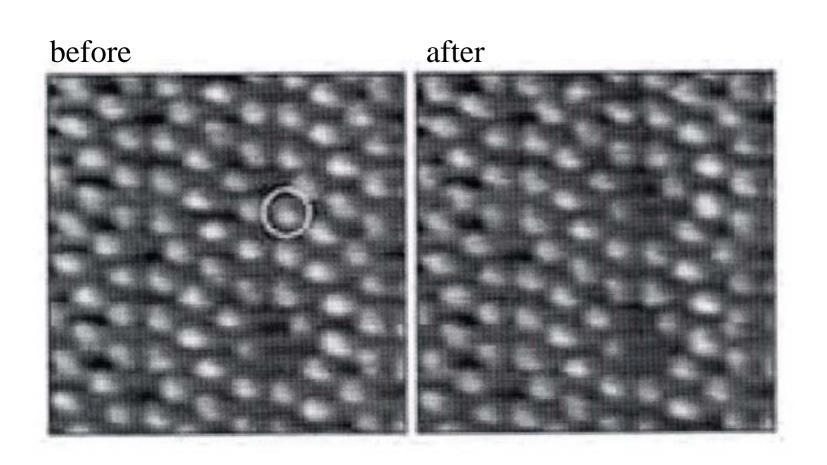


Feedback circuit



## Control of individual atoms by the tip of Nc-AFM (S.Morita, Osaka Univ.)

Any target atoms can be removed by the ncAFM tip



## Theoretical Problems of ncAFM

How the *atomic scale force* influences on the *cantilever oscillation* and how is it measured by *ncAFM images*?

Frequency shift, Energy dissipation

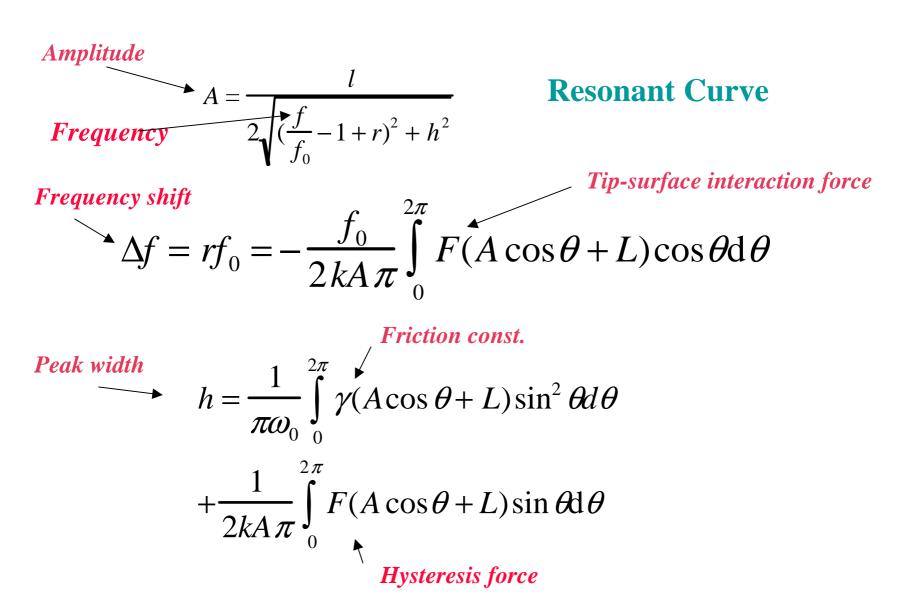
How the ncAFM images can be simulated by the calculated *tip-surface* force, deformation, or atomistic irreversible processes?

Effect of tip atomic structure and atom kinds?

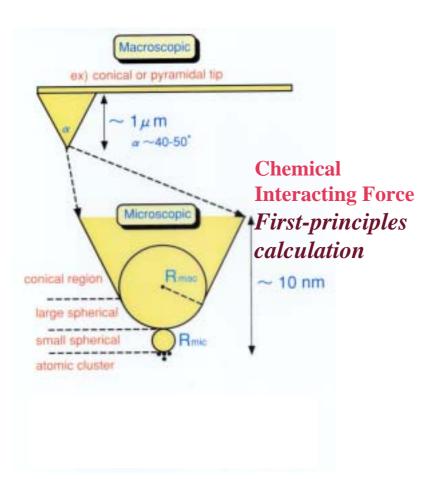
Effect of reversible/irreversible structure change?

How the dynamic surfaces are observed?

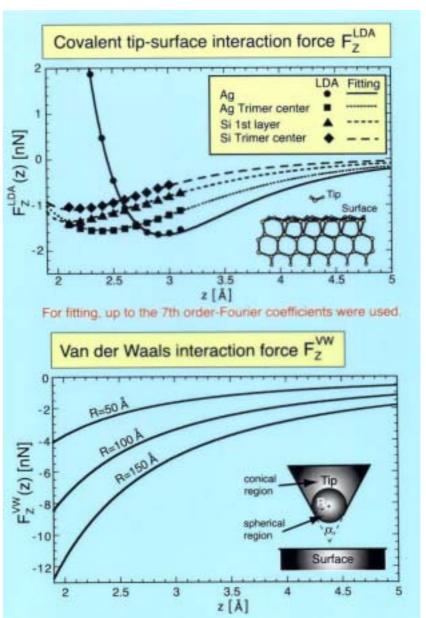
#### Macroscopic observable quantities and atomic scale interaction



## Simulation by the first-principles method



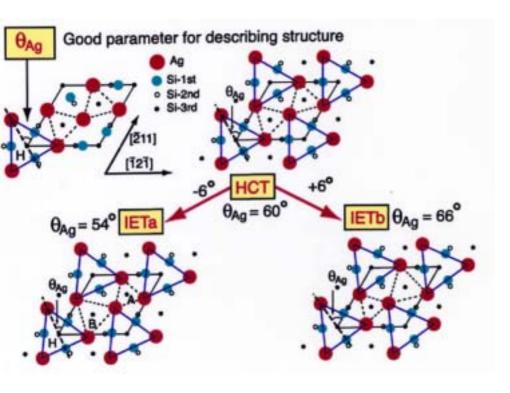
Van der Waals Force Calculation with a continuum model



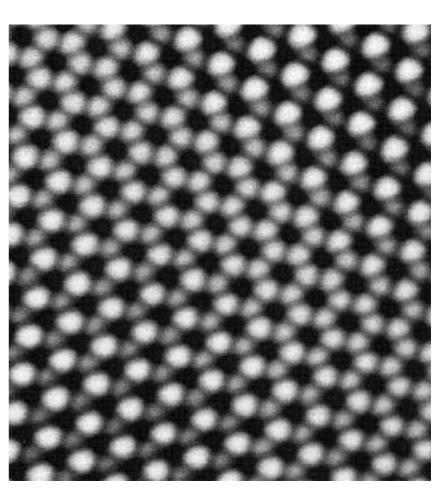
## IET structure of Si(111) 3 $\times$ 3 -Ag surface

#### STM image of at 62K by Hasegawa

#### IET structure and HCT structure

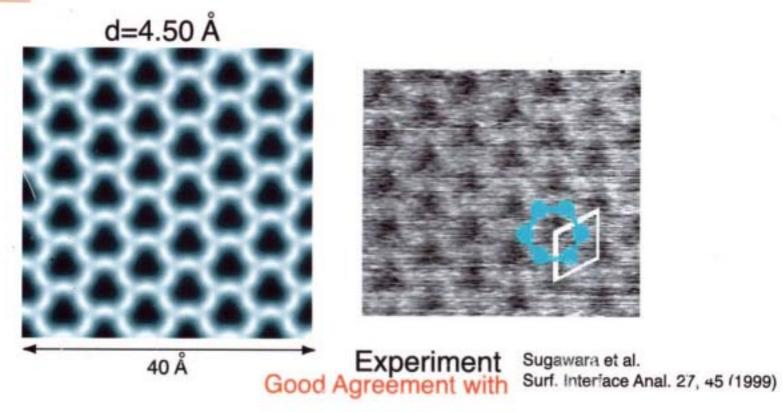


H.Aizawa et al, Surface Sci., 429(1999)509



## NC-AFM Images at Room Temperature

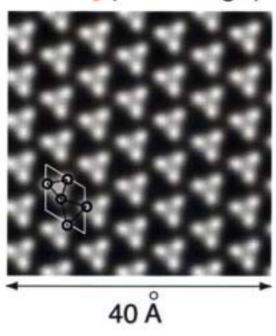
T = 300 K

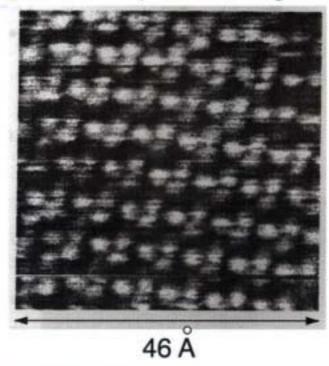


N.Sasaki, S.Watanabe and M. Tsukada

## NC-AFM Image at Low Temperature

Theory(IET Image) Experiment (Morita, Sugawara Group)





T=6.2 K

IET structure appears in the low temperature NC-AFM experiment by Osaka Univ. group.

Low tempeature experiment is reproduced!!

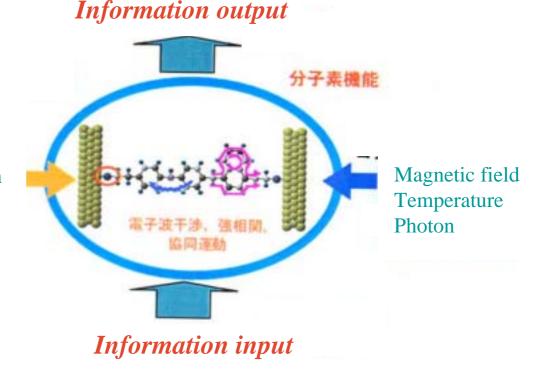
## Atom bridges and Molecular bridges

Quantum transport FET, Switches Memories, Sensors Molecular spintronics Light emission

Novel quantum devices Using coherent states

non-locality,
multiplicity,
quantum entanglement,
Instantaneous
operation,

Electron Spin



# Methods of the calculation for open non-equilibrium systems

First-Principles Recursion Transfer Matrix Method (FP -RTM)

Lippman-Schwinger, non-local pseudopotential

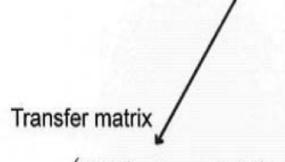
Density Functional Method/Tight-Binding Method + Non-equilibrium Green's Function Method (DF-TB+NE-GF)

parameters determined by DFT( TAPP, Gaussian etc)

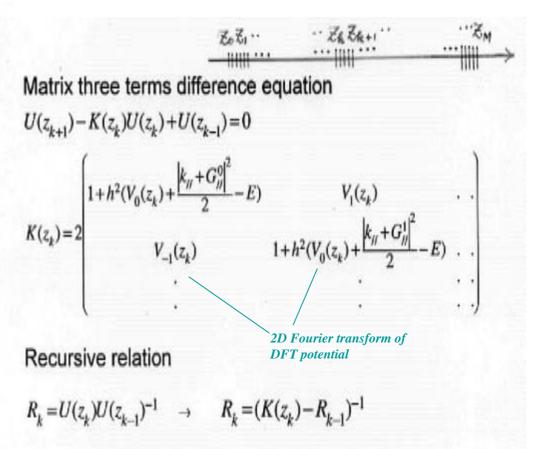
#### First-Principles

#### Recursion Transfer Matrix Method

$$\Psi_n(\mathbf{r}_{//},z_k) = \exp(i\mathbf{k}_{//}\mathbf{r}_{//}) \sum_m \underline{\Psi_n(\mathbf{G}_{//}^m,z_k)} \exp(i\mathbf{G}_{//}^m\mathbf{r}_{//})$$

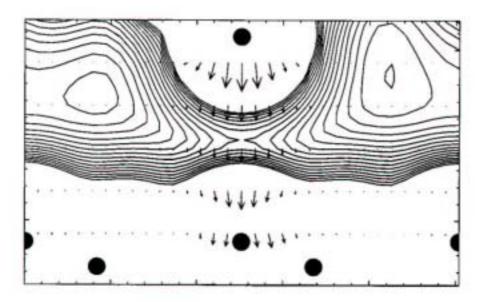


$$U(z_k) = \begin{pmatrix} \Psi_0(\mathbf{G}_{//}^0, z_k) & \dots & \Psi_N(\mathbf{G}_{//}^0, z_k) \\ \vdots & \ddots & \vdots \\ \Psi_0(\mathbf{G}_{//}^N, z_k) & \dots & \Psi_N(\mathbf{G}_{//}^N, z_k) \end{pmatrix}$$



With an appropriate boundary condition, R and U are calculated From the right and left electrode wave-functions DFT potential determined. This is equivalent to Non-equilibrium Green's function approach.

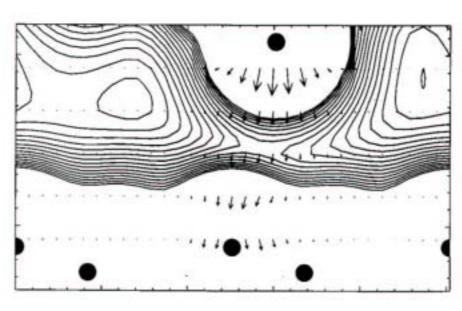
## Barrier and Current Density



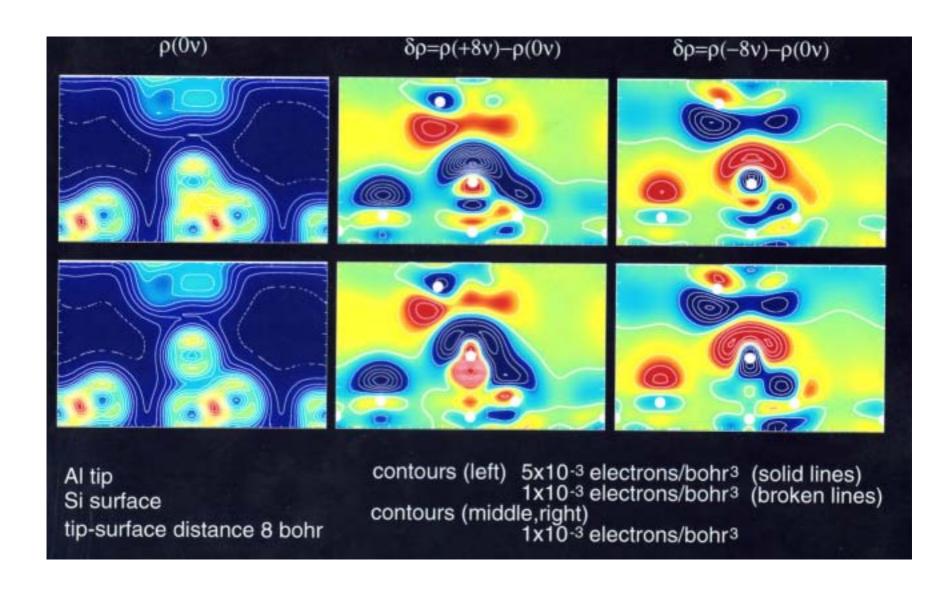
d=12au Al tip

 $V_s=2V$ 

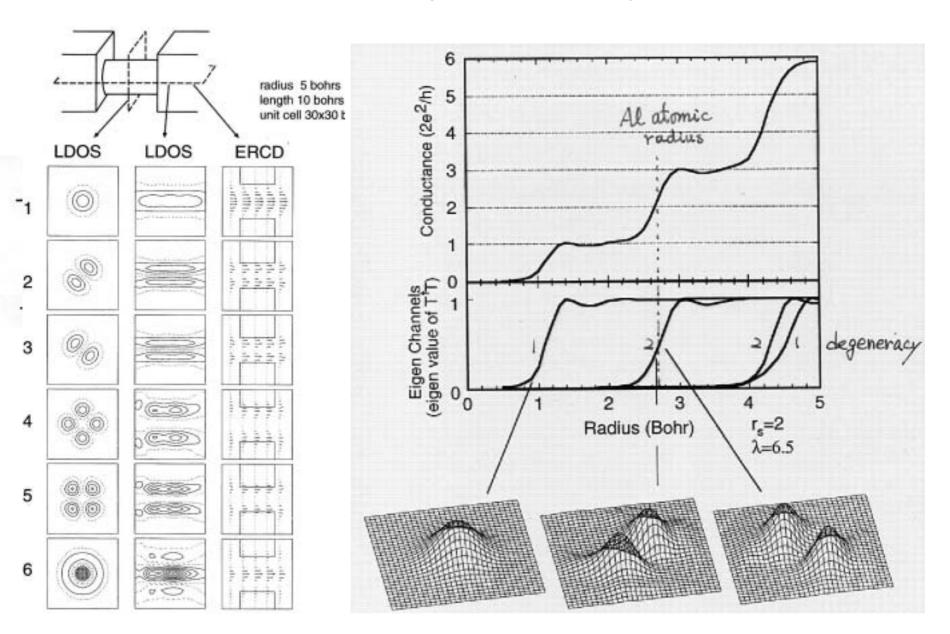
Si surface



## Al探針によるSi表面からの原子引き抜き

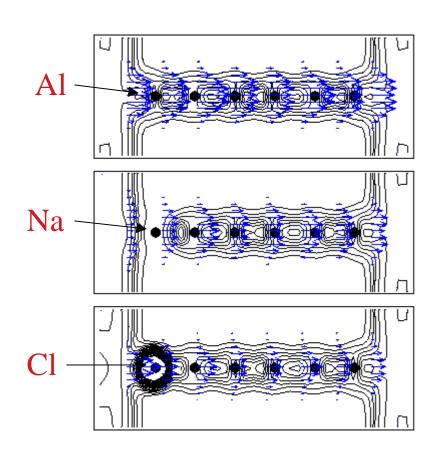


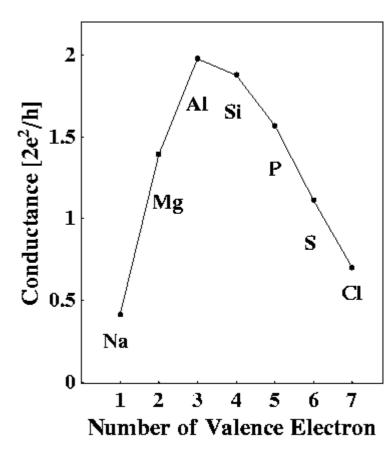
## Conductance of Jellium Cylinder



## Conductance through Al atomic-wires with various atoms mixed at contacts

K.Hirose, N.Kobayashi, M.Tsukada, to be appeared/ nonlocal p.p.

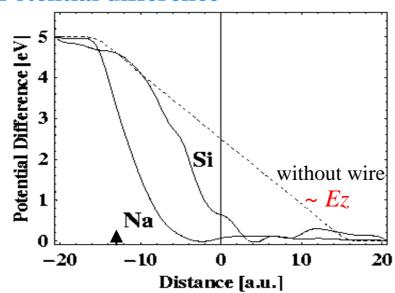




## Where does the bias drop in the wire?

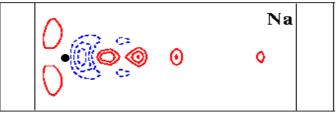
#### **Potential difference**

Bias = 5V

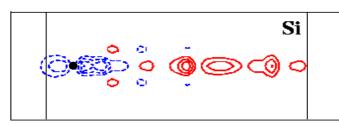


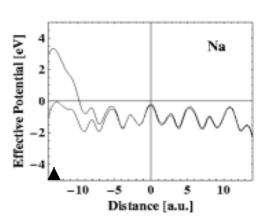
Charge difference  $(\rho(\mathbf{r},5V) - \rho(\mathbf{r},0V))$ 

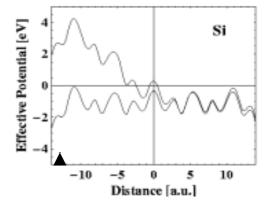
Local polarization (s-orbital)



Spread-out (p-orbital)



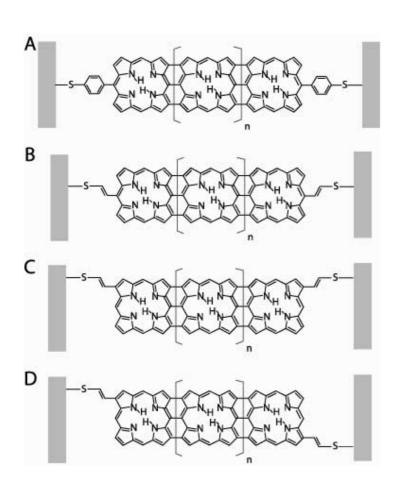


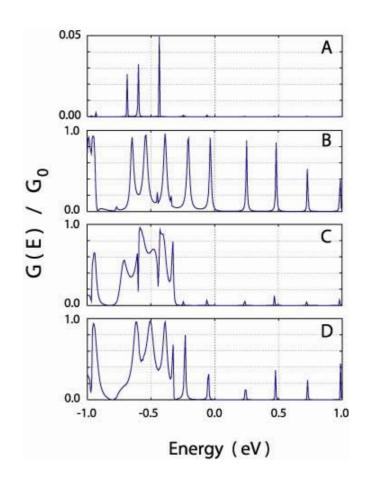


Bias drop is determined by the local polarization.

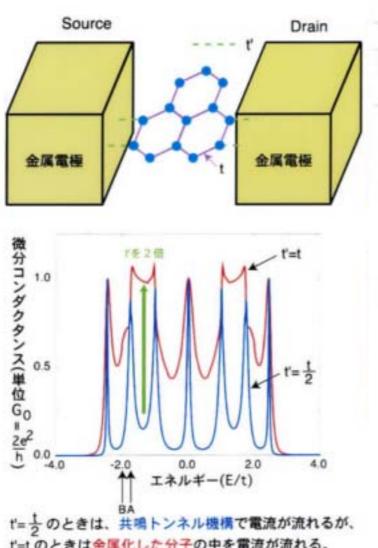
One impurity gives a significant influence!

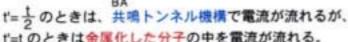
## Transmission Spectra of tape-porphyrin molecules

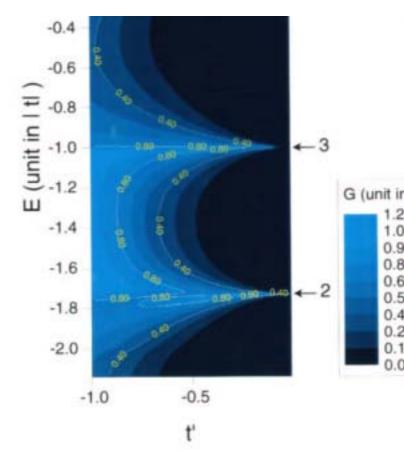




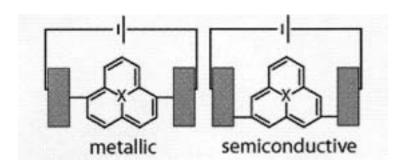
## Transmission spectrum of phenalenyl molecule

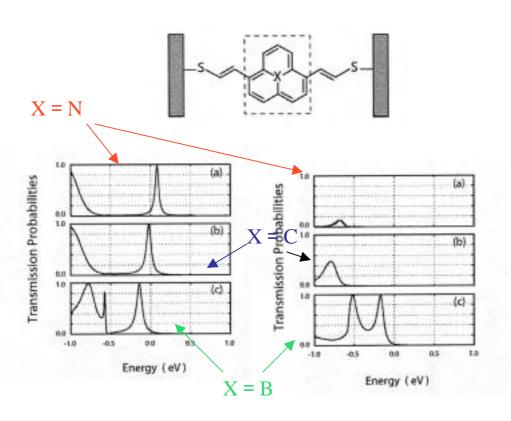


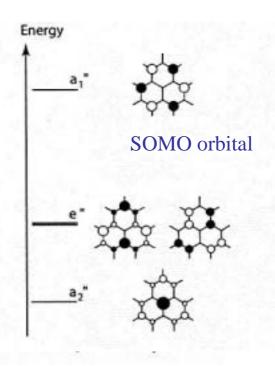


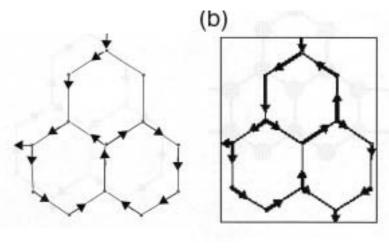


### Phenalenyl based molecules



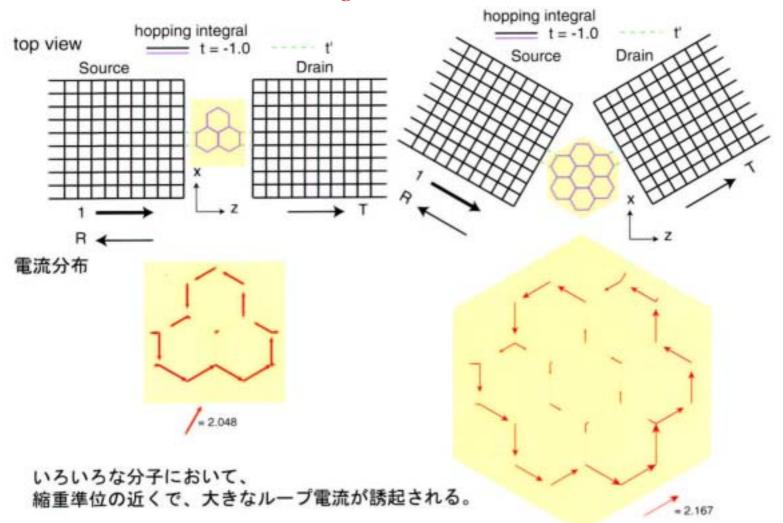




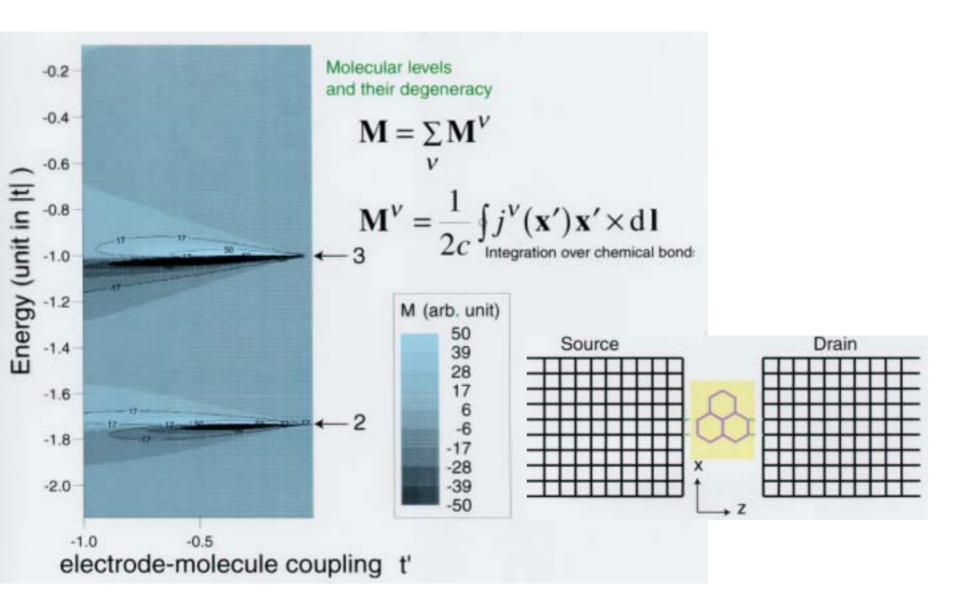


## Induced large loop current

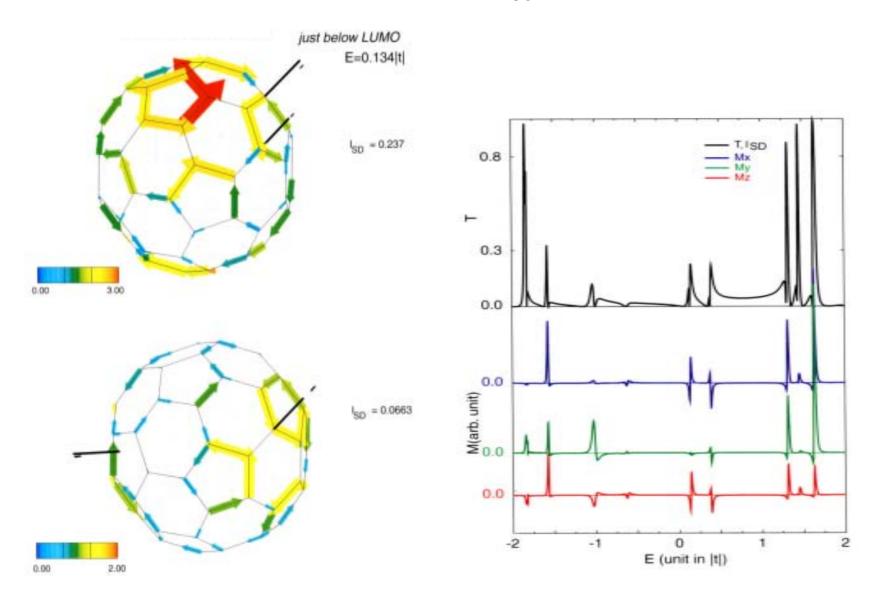
near degenerate levels



## Condition for the large loop current



## Transmission of Fullerene $C_{60}$ and loop current



## 分子デバイスのシミュレーション課題

- \*基板電極との接続
- \*興味ある分子の探索
- \*分子架橋3端子系
- (量子ゲート/スイッチ、量子機能)
- \*スピン、永久電流、内部電流、動的過程
- \*分子架橋近藤系
- \*デコヒーレンス、分子Qビット
- \*単電子過程とコヒ・レンス過程の協奏

#### 将来展望

